## AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings of claims in the application:

## LISTING OF CLAIMS:

1. (original) A metal compound represented by general formula (I):

$$\mathbf{M} = \left( -0 - \begin{bmatrix} \mathbf{R}^1 \\ \mathbf{C} \\ \mathbf{R}^2 \end{bmatrix} - \mathbf{N} - \mathbf{R}^3 \right)_{\mathbf{R}}$$
 (I)

wherein  $R^1$ ,  $R^2$ ,  $R^3$ , and  $R^4$  each represent an alkyl group having 1 to 4 carbon atoms; A represents an alkanediyl group having 1 to 8 carbon atoms; M represents a lead atom, a titanium atom or a zirconium atom; n represents 2 when M is a lead atom or 4 when M is a titanium or zirconium atom.

- 2. (original) The metal compound according to claim 1, wherein A is a methylene group.
- 3. (currently amended) The metal compound according to claim 1 [[or 2]], wherein M is a lead atom.
- 4. (currently amended) The metal compound according to claim 1 [[or 2]], wherein M is a titanium atom.
- 5. (currently amended) The metal compound according to claim 1 [[or 2]], wherein M is a zirconium atom.

- 6. (currently amended) A material for thin film formation comprising the metal compound according to any one of claims 1 to 5 claim 1.
- 7. (currently amended) A material for thin film formation comprising the metal compound of claim 3, the metal compound of claim 4, and the metal compound of claim 5 a metal compound of formula (I), wherein M is a lead atom; a compound of formula (I), wherein M is a titanium atom; and a compound of formula (I), wherein M is a zirconium atom; and wherein the compound of formula (I) is the compound according to claim 1.
- . 8. (original) A material for thin film formation comprising the metal compound of claim 3, tetrakis(1-methoxy-2-methyl-2-propoxy)titanium, and tetrakis(1-methoxy-2-methyl-2-propoxy)zirconium.
- 9. (currently amended) A process for thin film formation comprising vaporizing the material for thin film formation according to claim 6,[[ 7 or 8,]] introducing the resulting vapor containing the metal compound onto a substrate, and causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.
- 10. (currently amended) A process for thin film formation comprising vaporizing a material for thin film formation containing the metal compound of claim 3, a material for thin-film formation containing the metal compound of claim 4, and a material for thin film formation containing the metal compound of claim 5 to obtain vapor containing the metal compounds, introducing the resulting vapor containing the metal compounds onto a substrate, and causing the vapor to decompose

and/or chemically react to form a metal-containing thin film on the substrate.

- 11. (original) A process for thin film formation comprising vaporizing a material for thin film formation containing the metal compound of claim 3, a material for thin film formation containing tetrakis(1-methoxy-2-methyl-2-propoxy)titanium, and a material for thin film formation containing tetrakis(1-methoxy-2-methyl-2-propoxy)zirconium to obtain vapor containing the metal compounds, introducing the resulting vapor containing the metal compounds onto a substrate, and causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.
- 12. (original) A process for thin film formation comprising vaporizing a material for thin film formation containing the metal compound of claim 3, a material for thin film formation containing tetra(tert-butoxy)titanium, and a material for thin film formation containing tetra(tert-butoxy)zirconium to obtain vapor containing the metal compounds, introducing the resulting vapor containing the metal compounds onto a substrate, and causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.
- 13. (new) A process for thin film formation comprising vaporizing a material for thin film formation containing the metal compound of claim 4, to obtain vapor containing the metal compounds, introducing the resulting vapor containing the metal compounds onto a substrate, and causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.

- 14. (new) A process for thin film formation comprising vaporizing a material for thin film formation containing the metal compound of claim 5, to obtain vapor containing the metal compounds, introducing the resulting vapor containing the metal compounds onto a substrate, and causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.
- 15. (new) A process for thin film formation comprising vaporizing the material for thin film formation according to claim 7, introducing the resulting vapor containing the metal compound onto a substrate, and causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.
- 16. (new) A process for thin film formation comprising vaporizing the material for thin film formation according to claim 8, introducing the resulting vapor containing the metal compound onto a substrate, and causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.
- 17. (new) The metal compound according to claim 2, wherein M is a lead atom.
- 18. (new) The metal compound according to claim 2, wherein M is a titanium atom.
- 19. (new) The metal compound according to claim 2, wherein  ${\tt M}$  is a zirconium atom.